Abstracts

Microwave noise and power performance of metamorphic InP heterojunction bipolar transistors (HBTs) (2001 Vol. III [MWSYM])

S. Halder, Y.Z. Xiong, G.I. Ng, H. Wang, H.Q. Zheng, K. Radhakrishnan and J.C.M. Hwang. "Microwave noise and power performance of metamorphic InP heterojunction bipolar transistors (HBTs) (2001 Vol. III [MWSYM])." 2001 MTT-S International Microwave Symposium Digest 01.3 (2001 Vol. III [MWSYM]): 1885-1888 vol.3.

For the first time, microwave noise and power performance of metamorphic InP HBTs (MM-HBTs) grown on GaAs substrates are reported. We find that microwave performance of MM-HBTs are comparable to that of lattice-matched InP HBTs (LM-HBTs) of identical design but fabricated on an InP substrate. The preliminary results imply that the superior performance of InP HBTs can be confidently exploited with the more mature manufacturing technology of GaAs.

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